

In the Claims

Claims 1-10 (Canceled).

11 (Original). A semiconductor structure comprising:

a surface including an exposed polymerizable dielectric and an exposed unpolymerizable region; and

a polymer selectively attached to said polymerizable dielectric to form a surface coating that selectively covers said polymerizable dielectric.

12 (Original). The structure of claim 11 wherein said unpolymerizable region is copper.

13 (Original). The structure of claim 11 wherein said polymer is a diffusion barrier and a copper layer is formed over said polymer.

14 (Original). The structure of claim 11 wherein said polymer is a seed layer and a copper layer is formed over said polymer.

15 (Original). The structure of claim 11 wherein said polymer is conductive.

16 (Original). The structure of claim 15 wherein said polymer is an oligomer.

17 (Original). The structure of claim 16 wherein said polymer is end-functionalized with vinyl groups.

18 (Original). The structure of claim 11 wherein said polymer acts as a copper diffusion barrier.

19 (Original). The structure of claim 11 wherein said polymer acts as a copper seed layer.

20 (Original). The structure of claim 11 wherein said polymer activates electroless deposition of a copper diffusion barrier.

21 (Original). The structure of claim 1 wherein said polymer is a monomer including palladium.

Claims 22-25 (Canceled).